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DDR4

K4A8G165WC-BITD



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Exceptional speed, high reliability, low energy consumption

High-performing memory empowers faster, powerful solutions. Samsung DDR4 delivers top speed with better bandwidth and reliability using less energy.

Specifications

Density	8 Gb	Org.	512M x 16
Speed	2666 Mbps	Voltage	1.2 V
Temp.	-40 ~ 95 °C	Package	96FBGA
Product Status	Mass Production		

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